

查询"2SC4441"供应商



**2SC4441**

NPN Triple Diffused Planar Silicon Transistor  
**Very High-Definition Monocuro Display**  
**Horizontal Deflection Output Applications.**

**Features**

- High reliability(Adoption of HVP process).
- High fast.
- High breakdown voltage.
- Wide ASO.
- Adoption of MBIT process.
- Micaless package facilitating mounting.

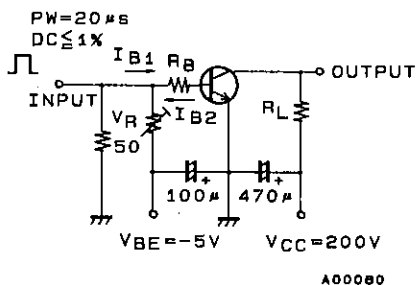
**Absolute Maximum Ratings at Ta = 25°C**

			unit
Collector-to-Base Voltage	V <sub>CB0</sub>	600	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>	400	V
Emitter-to-Base Voltage	V <sub>EBO</sub>	7	V
Collector Current	I <sub>C</sub>	10	A
Peak Collector Current	i <sub>cp</sub>	PW ≤ 300μs, Duty Cycle ≤ 10%	
Collector Dissipation	P <sub>C</sub>	2.0	W
		T <sub>c</sub> = 25°C	
Junction Temperature	T <sub>j</sub>	35	W
Storage Temperature	T <sub>stg</sub>	150	°C
		-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 400V, I <sub>E</sub> = 0			10	μA
	I <sub>CES</sub>	V <sub>CE</sub> = 600V			0.5	mA
Collector Sustain Voltage	V <sub>CEO(sus)</sub>	I <sub>C</sub> = 100mA, I <sub>B</sub> = 0	400			V
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0			1	mA
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 6A, I <sub>B</sub> = 1.2A			0.8	V
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 6A, I <sub>B</sub> = 1.2A			1.5	V
DC Current Gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 1.2A	15			
	h <sub>FE(2)</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 6A	10		20	
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.2A		20		MHz
Storage Time	t <sub>stg</sub>	I <sub>C</sub> = 7A, I <sub>B1</sub> = 1.4A I <sub>B2</sub> = -2.8A, R <sub>L</sub> = 28.6Ω V <sub>CC</sub> = 200V			3.0	μs
Fall Time	t <sub>f</sub>				0.2	μs

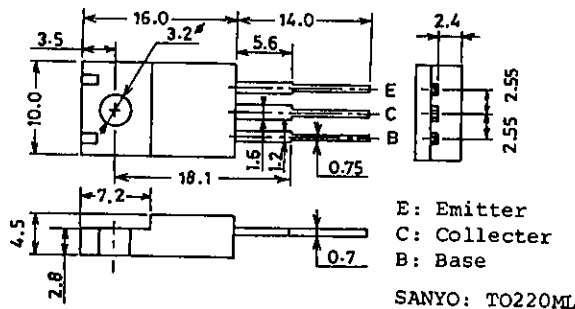
**Switching Time Test Circuits**



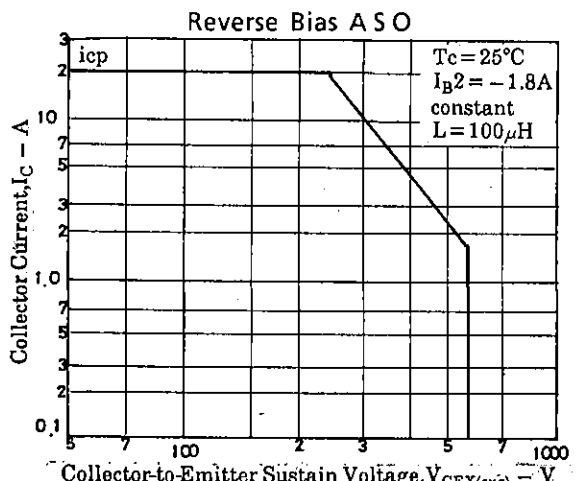
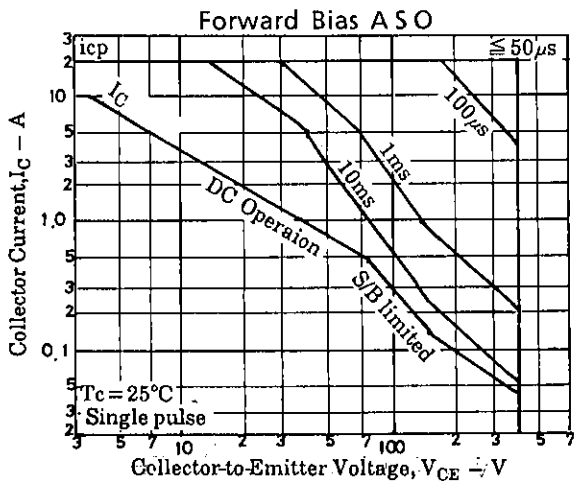
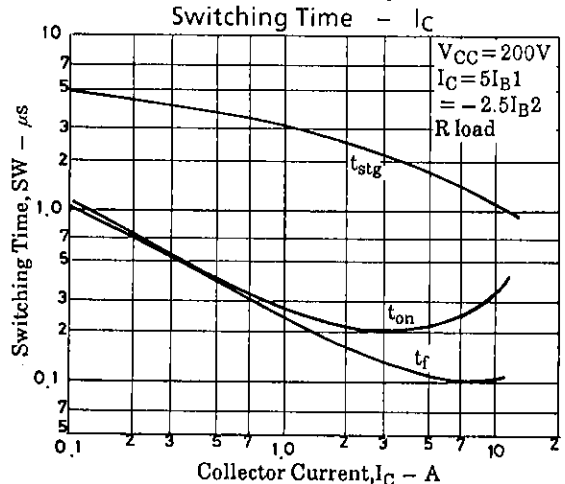
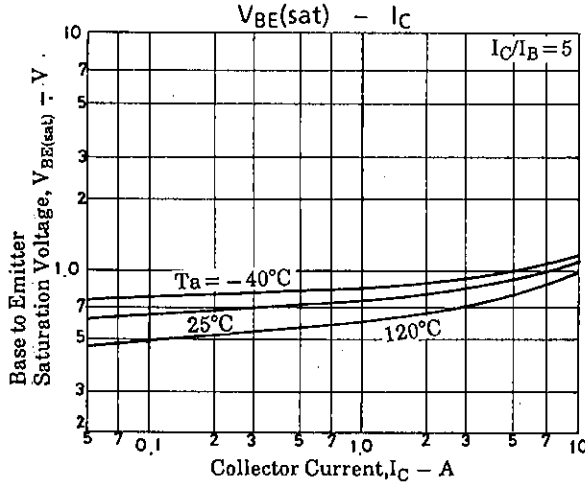
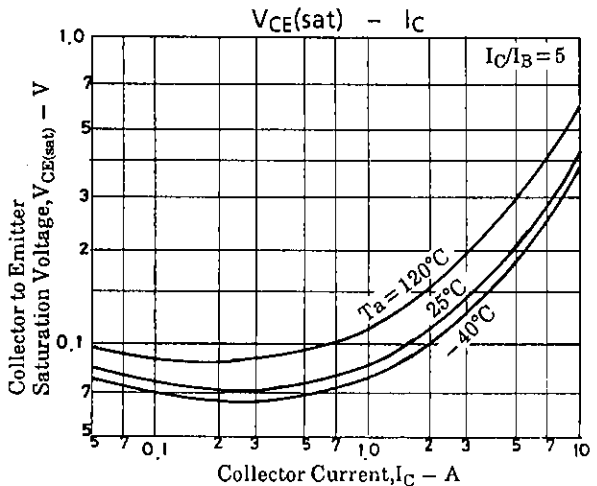
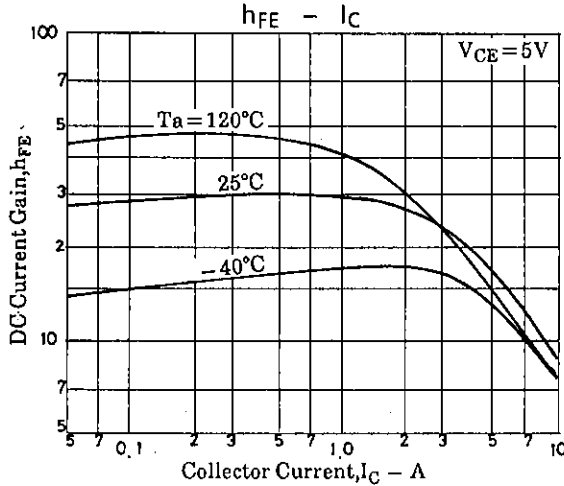
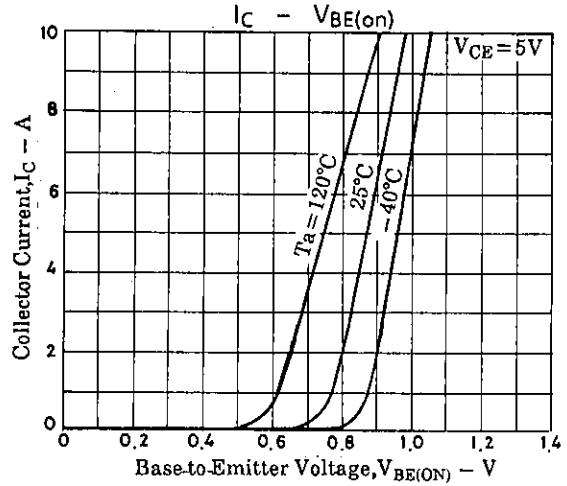
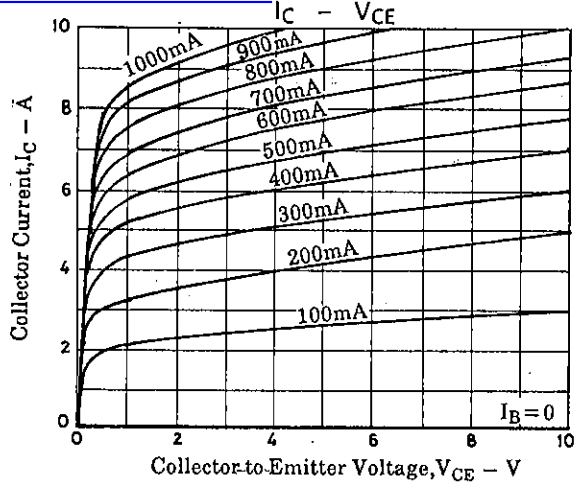
Unit (resistance:Ω, capacitance:F)

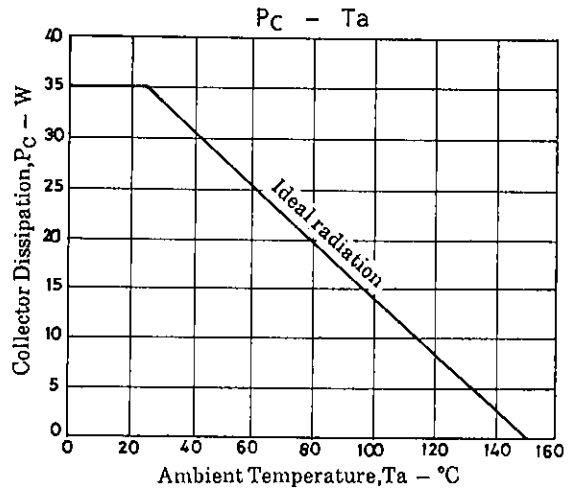
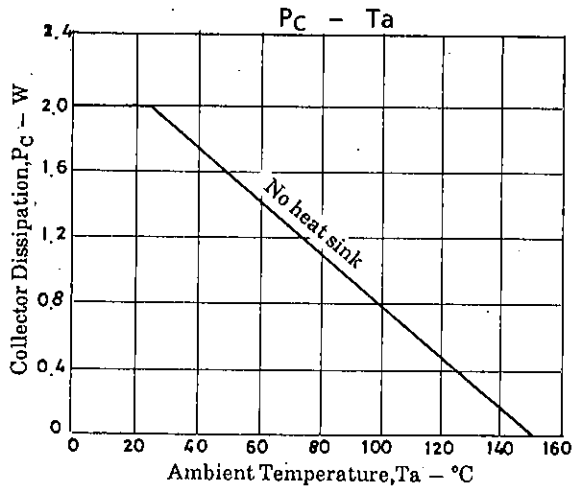
**Package Dimensions**

(unit: mm) 2041



E: Emitter  
 C: Collector  
 B: Base  
 SANYO: TO220ML





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